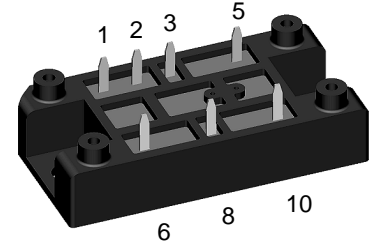
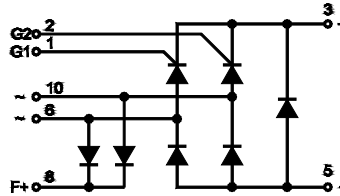


# Half Controlled Single Phase Rectifier Bridge

Including Freewheeling Diode and Field Diodes

$V_{RRM} = 800-1600\text{ V}$   
 $I_{dAVM} = 21\text{ A}$

$V_{RSM}$ $V_{DSM}$ V	$V_{RRM}$ $V_{DRM}$ V	Type
900	800	VHFD 16-08io1
1300	1200	VHFD 16-12io1
1500	1400	VHFD 16-14io1
1700	1600	VHFD 16-16io1



## Bridge and Freewheeling Diode

Symbol	Test Conditions	Maximum Ratings
$I_{dAV}$	$T_H = 85^\circ\text{C}$ , module	16 A
$I_{dAVM}$ ①	module	21 A
$I_{FRMS}$ , $I_{TRMS}$	per leg	15 A
$I_{FSM}$ , $I_{TSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $V_R = 0\text{ V}$	$t = 10\text{ ms}$ (50 Hz), sine 150 A $t = 8.3\text{ ms}$ (60 Hz), sine 170 A
	$T_{VJ} = T_{VJM}$ $V_R = 0\text{ V}$	$t = 10\text{ ms}$ (50 Hz), sine 130 A $t = 8.3\text{ ms}$ (60 Hz), sine 140 A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0\text{ V}$	$t = 10\text{ ms}$ (50 Hz), sine 110 $\text{A}^2\text{s}$ $t = 8.3\text{ ms}$ (60 Hz), sine 120 $\text{A}^2\text{s}$
	$T_{VJ} = T_{VJM}$ $V_R = 0\text{ V}$	$t = 10\text{ ms}$ (50 Hz), sine 85 $\text{A}^2\text{s}$ $t = 8.3\text{ ms}$ (60 Hz), sine 80 $\text{A}^2\text{s}$
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $f = 50\text{ Hz}$ , $t_p = 200\ \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3\text{ A}$ , $di_G/dt = 0.3\text{ A}/\mu\text{s}$	repetitive, $I_T = 50\text{ A}$ 150 $\text{A}/\mu\text{s}$ non repetitive, $I_T = 0.5 I_{dAV}$ 500 $\text{A}/\mu\text{s}$
	$T_{VJ} = T_{VJM}$ ; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	1000 $\text{V}/\mu\text{s}$
$V_{RGM}$		10 V
$P_{GM}$	$T_{VJ} = T_{VJM}$ $I_T = 0.5 I_{dAVM}$	$t_p = 30\ \mu\text{s}$ $\leq 10\text{ W}$ $t_p = 500\ \mu\text{s}$ $\leq 5\text{ W}$ $t_p = 10\text{ ms}$ $\leq 1\text{ W}$
		0.5 W
	$P_{GAVM}$	
$T_{VJ}$		-40...+125 $^\circ\text{C}$
$T_{VJM}$		125 $^\circ\text{C}$
$T_{stg}$		-40...+125 $^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ min}$ 3000 V~ $t = 1\text{ s}$ 3600 V~
	$d_s$	Creep distance on surface 12.7 mm
$d_A$	Strike distance in air 9.4 mm	
$a$	Max. allowable acceleration 50 $\text{m}/\text{s}^2$	
$M_d$	Mounting torque (M5)	2-2.5 Nm
	(10-32 UNF)	18-22 lb.in.
Weight		35 g

### Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Blocking voltage up to 1600 V
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered E 72873

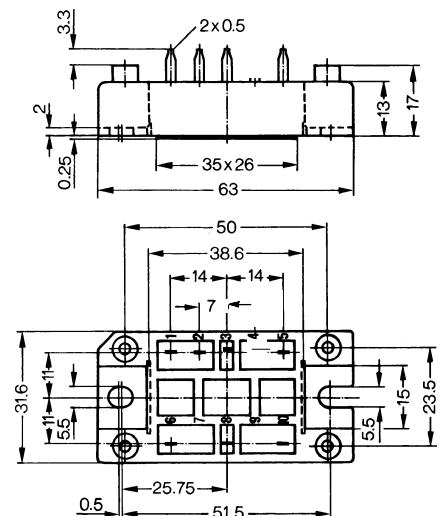
### Applications

- Supply for DC power equipment
- DC motor control

### Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

### Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values
$I_R, I_D$	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	$\leq 5$ mA $\leq 0.3$ mA
$V_T, V_F$	$I_T, I_F = 45$ A; $T_{VJ} = 25^\circ\text{C}$	$\leq 2.55$ V
$V_{T0}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	1.0 V
$r_T$		40 m $\Omega$
$V_{GT}$	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 1.0$ V $\leq 1.2$ V
$I_{GT}$	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	$\leq 65$ mA $\leq 80$ mA $\leq 50$ mA
$V_{GD}$	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	$\leq 0.2$ V
$I_{GD}$	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	$\leq 5$ mA
$I_L$	$I_G = 0.3$ A; $t_g = 30$ $\mu\text{s}$ ; $di_G/dt = 0.3$ A/ $\mu\text{s}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	$\leq 150$ mA $\leq 200$ mA $\leq 100$ mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	$\leq 100$ mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 0.5V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ $\mu\text{s}$	$\leq 2$ $\mu\text{s}$
$t_q$	$T_{VJ} = 125^\circ\text{C}; I_T = 15$ A, $t_p = 300$ $\mu\text{s}$ , $V_R = 100$ V	typ. 150 $\mu\text{s}$
$Q_r$	$di/dt = -10$ A/ $\mu\text{s}$ , $dv/dt = 20$ V/ $\mu\text{s}$ , $V_D = 2/3 V_{DRM}$	75 $\mu\text{C}$
$R_{thJC}$	per thyristor (diode); DC current	2.4 K/W
	per module	0.6 K/W
$R_{thJH}$	per thyristor (diode); DC current	3.0 K/W
	per module	0.75 K/W

### Field Diodes

Symbol	Test Conditions	Maximum Ratings
$I_{FAV}$	$T_H = 85^\circ\text{C}$ , per Diode	4 A
$I_{FAVM}$	per diode	4 A
$I_{FRMS}$	per diode	6 A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C};$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine 100 A $t = 8.3$ ms (60 Hz), sine 110 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine 85 A $t = 8.3$ ms (60 Hz), sine 94 A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine 50 A <sup>2</sup> s $t = 8.3$ ms (60 Hz), sine 50 A <sup>2</sup> s
	$T_{VJ} = T_{VJM}$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine 36 A <sup>2</sup> s $t = 8.3$ ms (60 Hz), sine 37 A <sup>2</sup> s
$I_R$	$V_R = V_{RRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	1 mA 0.15 mA
$V_F$	$I_F = 21$ A; $T_{VJ} = 25^\circ\text{C}$	1.83 V
$V_{T0}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.9 V
$r_T$		50 m $\Omega$
$R_{thJC}$	per diode; DC current	4.4 K/W
$R_{thJH}$	per diode; DC current	5.2 K/W

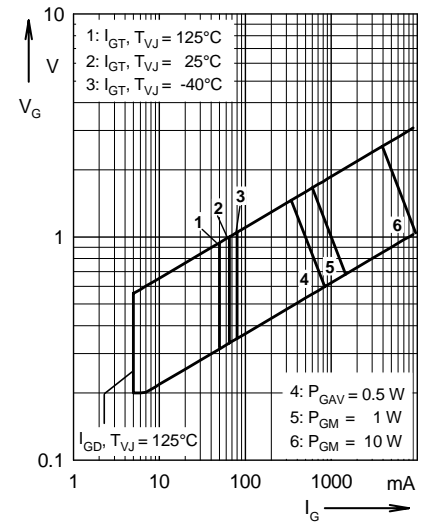


Fig. 1 Gate trigger range

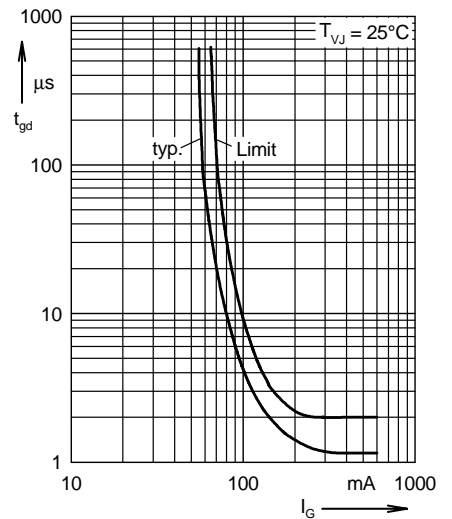


Fig. 2 Gate controlled delay time  $t_{gd}$

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

① for resistive load

IXYS reserves the right to change limits, test conditions and dimensions.

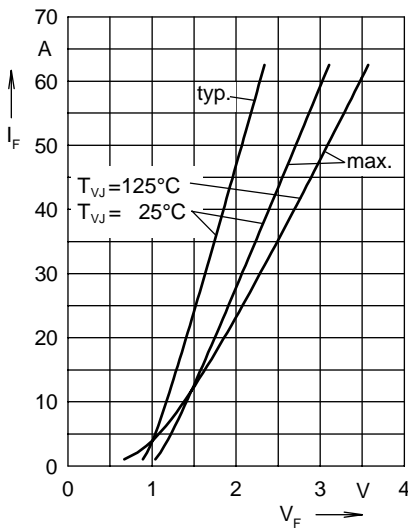


Fig. 3 Forward current versus voltage drop per diode

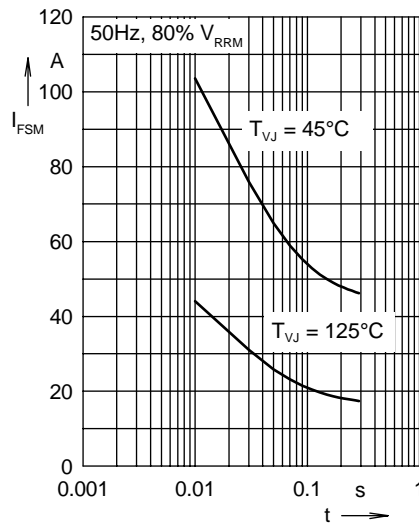


Fig. 4 Surge overload current

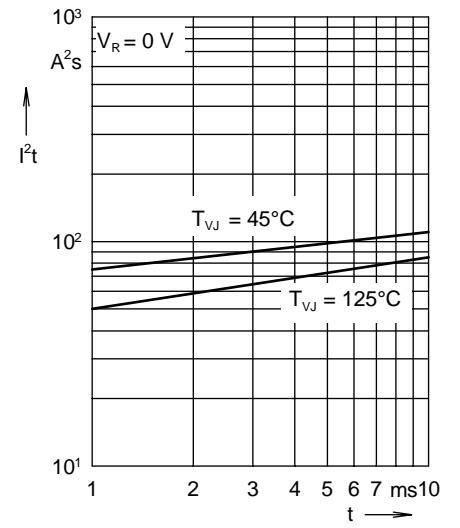


Fig. 5  $I^2t$  versus time per diode

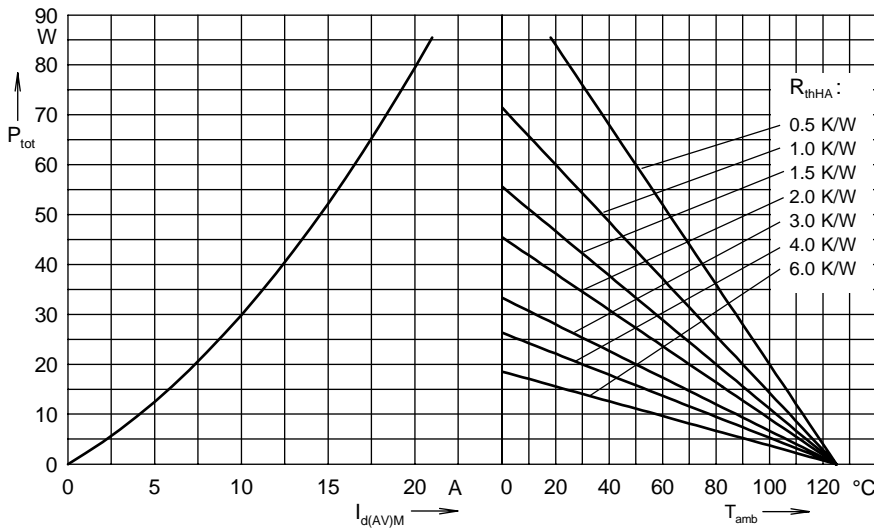


Fig. 6 Power dissipation versus direct output current and ambient temperature

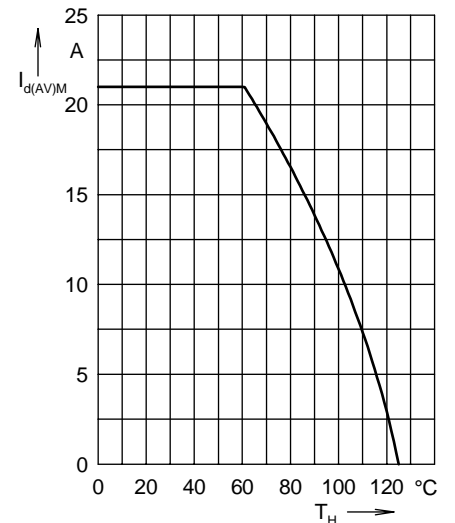


Fig. 7 Max. forward current versus heatsink temperature

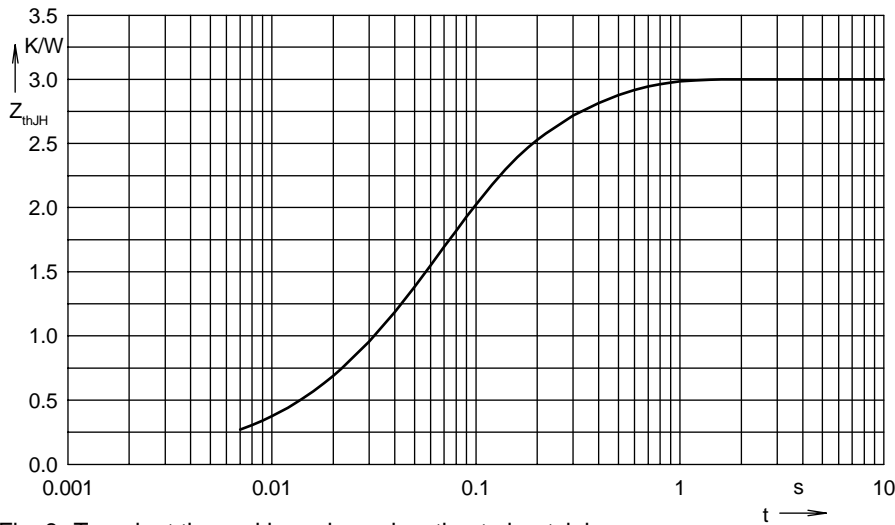


Fig. 8 Transient thermal impedance junction to heatsink

Constants for  $Z_{thJH}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.01	0.008
2	0.4	0.05
3	1.69	0.06
4	0.9	0.25